L Number	Hits	Search Text	DB	Time stamp
2	10	5786275.pn. 6482743.pn. 6451697.pn. 6569349.pn.	USPAT;	2004/01/05 10:08
		6579153.pn. 6602436.pn. 6616717.pn. 20010024933.pn.	US-PGPUB	
		20020058426.pn. 20030022497.pn.		
3	39	5676587.pn. 5853604.uref. 5827781.uref.	USPAT;	2004/01/05 11:49
			US-PGPUB	
4	8	5733177.uref.	USPAT;	2004/01/05 12:01
•	_		US-PGPUB	
5	16	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/01/05 12:02
·	20	conduct\$4 metal))) same (relative near2 (speed velocity))	US-PGPUB	,
6	132	((438/626.ccls, 438/633.ccls, 438/687.ccls, 438/690.ccls,	USPAT;	2004/01/05 12:15
١ ١	152	438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	200 1, 02, 00 22120
		near2 (speed velocity))) and ((cmp (chemical near	55 / 5/ 55	
		mechanical)) with (copper cu conduct\$4 metal))		
7	8	((438/626.ccls, 438/633.ccls, 438/687.ccls,) and	USPAT;	2004/01/05 12:44
<i>'</i>	0	(438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.))	US-PGPUB	2004/01/03 12.11
			03-40400	
•	25	and (relative near2 (speed velocity)) (((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/01/05 12:49
8	25			2007/01/03 12.73
		conduct\$4 metal))) same ((relative linear) near2 (speed	US-PGPUB	
_		velocity))	UCDAT.	2004/01/05 12:56
9	28	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2004/01/05 12:56
		conduct\$4 metal))) same ((rotat\$6 near2 (speed velocity))	US-PGPUB	
	_	rpm rpms) same (change decreas\$4 reduc\$5)	500 100	2004/04/05 42:00
10	4	(((cmp (chemical near mechanical)) with (copper cu	EPO; JPO;	2004/01/05 13:08
		conduct\$4 metal))) and (relative near2 (speed velocity))	DERWENT;	
			IBM_TDB	
11	109	(cmp (chemical near mechanical) polish\$4) and ((carrier	USPAT;	2004/01/05 13:09
		head) same (retain\$4 ring) same membrane same (platen	US-PGPUB	
		pad) same (pressure psi pa)) and (wafer substrate)		
12	146	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2004/01/05 13:52
		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp	US-PGPUB	
		(chemical near mechanical) polish\$4) with (copper cu		
		conduct\$4 metal)) and ((carrier head) same (retain\$4 ring		
		membrane) same (platen pad) same (pressure psi pa)) and	1	
		(wafer substrate))		
13	137	((cmp (chemical near mechanical) polish\$4) and ((carrier	EPO; JPO;	2004/01/05 14:15
		head) same (retain\$4 ring membrane)) and (platen pad))	DERWENT;	
		and (pressure psi pa copper cu metal conduct\$4)	IBM_TDB	
14	6	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/01/05 14:22
		substrate) and ((carrier head) same (platen pad) same (rpm	US-PGPUB	
		adj second))		
15	0	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/01/05 14:31
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		((rpm rotat\$6) near accelerat\$5))		
16	2	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/01/05 14:31
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		((rpm rotat\$6) with accelerat\$5))		
17	30	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2004/01/05 14:33
	1	substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
		accelerat\$5)		
19	480	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2004/01/05 14:36
		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	
		near2 (speed velocity))		
20	626	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2004/01/05 14:43
20	020	438/691.ccls. 438/692.ccls. 451/41.ccls.) and ((cmp	US-PGPUB	
		(chemical near mechanical) polish\$4) and ((carrier head)		:
		same (retain\$4 ring membrane)) and (wafer substrate) and		
		(platen pad))		
	ı	(Piacei Pau)		